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**Listing of Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claim 1 (Previously Presented): A method for producing a silicon single crystal, wherein the silicon single crystal is pulled while doping with carbon and controlling V/G (V: crystal pulling rate, G: crystal solid-liquid interface temperature gradient along a growing axis) to have an N-region over an entire plane of the crystal, the silicon single crystal being pulled at a rate greater than the rate of pulling a silicon single crystal with no carbon doping, and in which the silicon single crystal is grown in accordance with Czochralski method.

Claim 2 (Previously Presented): The method for producing a silicon single crystal according to claim 1, wherein the silicon single crystal is doped with nitrogen as well as carbon in which the CZ silicon single crystal is grown.

Claim 3 (Previously Presented): The method for producing a silicon single crystal according to claim 1, wherein the silicon single crystal is pulled while doping with carbon having concentration of 0.1 ppma or more and controlling V/G within a range of 0.183 to 0.177 mm<sup>2</sup>/K·min.

Claim 4 (Previously Presented): The method for producing a silicon single crystal according to claim 2, wherein a silicon single crystal is pulled while doping with carbon having concentration of 0.1 ppma or more and controlling V/G within a range of 0.183 to 0.177 mm<sup>2</sup>/K·min.

Claim 5 (Previously Presented): A method for producing a silicon single crystal, wherein the silicon single crystal produced by the method according to claim